


FORM PTO-1449	SERIAL NO. Not yet assigned	CASE NO. 10322/57 Client Ref. No. TF03009
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)	FILING DATE Herewith	GROUP ART UNIT Not yet assigned
APPLICANT(S): Kuang-Chien Hsieh et al.		

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	NAME	CLASS/ SUBCLASS	FILING DATE

FOREIGN PATENT DOCUMENTS


EXAMINER INITIAL	DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO

EXAMINER INITIAL	OTHER ART - NON PATENT LITERATURE DOCUMENTS <small>(Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)</small>	
	A1	L.J. Chou, K.C. Hsieh, D.E. Wohler and K.Y. Cheng, <i>Formation of Amorphous Aluminum Oxide and Gallium Oxide on InP Substrates by Water Vapor Oxidation</i> , American Institute of Physics, pgs. 6932-6934, December 15, 1998.
	A2	L.J. Chou, K.C. Hsieh, A. Moy, D.E. Wohler, G. Pickrell and K.Y. Cheng, <i>Improving the Al-Bearing Native-Oxide/GaAs Interface Formed by Wet Oxidation with a Thin GaP Barrier Layer</i> , American Institute of Physics, pgs. 2722-2724, May 25, 2003.

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	A3	K. L. Chang, G.W. Pickrell, D.E. Wohler, J.H. Eppe, H.C. Lin, K.Y. Cheng and K.C. Hsieh, <i>Microstructure and Wet Oxidation of Low-Temperature-Grown Amorphous (Al/Ga,As)</i> , American Institute of Physics, Vol. 89 No. 1, pgs. 747-752, January 1, 2001.
	A4	J.J. Eppe, K.L. Chang, C.F. Xu, G.W. Pickrell, K.Y. Chang, and K.C. Hsieh, <i>Formation of Highly Conductive Polycrystalline GaAs from Annealed Amorphous (Ga,As)</i> , American Institute of Physics, pgs. 5331-5336, May 1, 2003.
	A5	H.C. Lin, W.H. Wang, K.C. Hsieh and K.Y. Cheng, <i>Fabrication of 1.55µm VCSELs on Si Using Metallic Bonding</i> , Electronics Letters, Vol. 38 No. 11, May 23, 2002.
	A6	H.C. Lin, K.L. Chang, K.C. Hsieh, K.Y. Cheng, <i>Metallic Wafer Bonding for the Fabrication of Long-Wavelength Vertical-Cavity Surface-Emitting Lasers</i> , Journal of Applied Physics, Vol. 92 No. 7, pgs. 4132-4134, October 1, 2002.
	A7	H.C. Lin, K.L. Chang, G.W. Pickrell, K.C. Hsieh and K.Y. Cheng, <i>Low Temperature Wafer Bonding by Spin on Glass</i> , Journal of Vacuum Science & Technology B, Vol. 20 No. 2, pgs. 752-754, March/April 2002..
	A8	G.W. Pickrell, K.L. Chang, J.H. Eppe, K.Y. Chang and K.C. Hsieh, <i>Protection of In_{0.25}Ga_{0.75}As/GaAs Structures During Lateral Oxidation Using an Amorphous InGaP Layer</i> , American Vacuum Society, Vol. 20 No. 3, pgs. 876-879, May/June 2002.
	A9	G.W. Pickrell, K.L. Chang, H.C. Lin, K.C. Hsieh and K.Y. Cheng, <i>Very-Low-Temperature Molecular Beam Epitaxial Growth of GaP/AlAs Heterostructures for Distributed Bragg Reflector Applications</i> , American Vacuum Society; pgs. 1536-1540, July/Aug. 2001.
	A10	G.W. Pickrell, H.C. Lin, K.L. Chang, K.C. Hsieh and K.Y. Cheng; <i>Fabrication of GaP/Al-Oxide Distributed Bragg Reflectors for the Visible Spectrum</i> , Applied Physics Letters, Vol. 78 No. 8, pgs. 1044-1046, February 19, 2001
	A11	Frank Shi, Scott MacLaren, Chaofeng Xu, K.Y. Cheng and K.C. Hsieh, <i>Hybrid-integrated GaAs/GaAs and InP/GaAs Semiconductors Through Wafer Bonding Technology: Interface Adhesion and Mechanical Strength</i> , American Institute of Physics, pgs. 5750-5756, May 1, 2003.
	A12	Frank F. Shi, Kuo-Lih Chang and Veronica I. Lai, <i>UltraWafer, Inc., A UIUC Semiconductor Start-up, Speeding Up What's Next</i> , pgs. 2-24,
	A13	D.E. Wohler, H.C. Lin, K.L. Chang, G.W. Pickrell, Jr., J.H. Eppe, K.C. Hsieh, K.Y. Cheng, <i>Fabrication of a Substrate-Independent Aluminum Oxide-GaAs Distributed Bragg Reflector</i> , Applied Physics Letters, Vol. 75 No. 10, pgs. 1371-1373, September 6, 1999.

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The references now cited are the following:

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